April 2013



# FGAF40N60SMD 600 V, 40 A Field Stop IGBT

# General Description

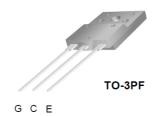
Using novel field stop IGBT technology, Fairchild<sup>®</sup>'s new series of field stop 2<sup>nd</sup> generation IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.

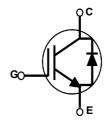
#### **Features**

- Maximum Junction Temperature : T<sub>J</sub> = 175°C
- Positive Temperaure Co-efficient for easy Parallel Operating
- · High Current Capability
- Low Saturation Voltage: V<sub>CE(sat)</sub> = 1.9 V(Typ.) @ I<sub>C</sub> = 40 A
- · High Input Impedance
- Fast Swiching: E<sub>OFF</sub> = 6.5 uJ/A
- · Tightened Parameter Distribution
- RoHS Compliant

#### **Applications**

- · Sewing Machine, CNC
- · Home Appliances, Motor-Control





#### **Absolute Maximum Ratings**

Symbol	Description		Ratings	Unit
V <sub>CES</sub>	Collector to Emitter Voltage		600	V
V <sub>GES</sub>	Gate to Emitter Voltage		± 20	V
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	80*	Α
'C	Collector Current	@ T <sub>C</sub> = 100°C	40*	А
I <sub>CM (1)</sub>	Pulsed Collector Current		120*	А
I <sub>F</sub>	Diode Forward Current	@ T <sub>C</sub> = 25°C	40*	А
	Diode Forward Current	@ T <sub>C</sub> = 100°C	20*	А
I <sub>FM (1)</sub>	Pulsed Diode Maximum Forward Current		120*	А
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	79	W
' D	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	39	W
T <sub>J</sub>	Operating Junction Temperature		-55 to +175	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

#### Notes:

\*Drain current limited by maximum junction temperature

1: Repetitive rating: Pulse width limited by max. junction temperature

#### **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	R <sub>θJC</sub> (IGBT) Thermal Resistance, Junction to Case		1.57	°C/W
$R_{\theta JC}(Diode)$	iode) Thermal Resistance, Junction to Case		3.27	°C/W
$R_{\theta JA}$	R <sub>0JA</sub> Thermal Resistance, Junction to Ambient		40	°C/W

# Package Marking and Ordering Information

<b>Device Marking</b>	Device	Package Reel Size		Tape Width	Quantity	
FGAF40N60SMD	FGAF40N60SMD	TO-3PF	-	-	30	

### Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics			•		
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V, I_{C} = 250\mu A$	600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_{J}}$	Temperature Coefficient of Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250μA	-	0.6	-	V/°C
I <sub>CES</sub>	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	250	μΑ
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	±400	nA
On Charac	teristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	I <sub>C</sub> = 250μA, V <sub>CE</sub> = V <sub>GE</sub>	3.5	4.5	6.0	V
02()		I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V	-	1.9	-	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage	I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V, T <sub>C</sub> = 175°C	-	2.1	-	٧
Dynamic C	haracteristics			•		
C <sub>ies</sub>	Input Capacitance		-	1880	-	pF
C <sub>oes</sub>	Output Capacitance	$V_{CE} = 30V_{,} V_{GE} = 0V_{,}$ f = 1MHz	-	180	-	pF
C <sub>res</sub>	Reverse Transfer Capacitance	- 1 - 11VII 12	-	50	-	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time		-	12	-	ns
t <sub>r</sub>	Rise Time		-	20	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>CC</sub> = 400V, I <sub>C</sub> = 40A,	-	92	-	ns
t <sub>f</sub>	Fall Time	$R_G = 6\Omega$ , $V_{GE} = 15V$ ,	-	13	17	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 25°C	-	0.87	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	0.26	0.34	mJ
E <sub>ts</sub>	Total Switching Loss		-	1.13	-	mJ
t <sub>d(on)</sub>	Turn-On Delay Time		-	15	-	ns
t <sub>r</sub>	Rise Time	$V_{CC} = 400V, I_C = 40A,$ $R_G = 6\Omega, V_{GE} = 15V,$	-	22	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		-	116	-	ns
t <sub>f</sub>	Fall Time		-	16	-	ns
E <sub>on</sub>	Turn-On Switching Loss	Inductive Load, T <sub>C</sub> = 175°C	-	0.97	-	mJ
E <sub>off</sub>	Turn-Off Switching Loss		-	0.60	-	mJ
E <sub>ts</sub>	Total Switching Loss	]	-	1.57	-	mJ

## Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
$Q_g$	Total Gate Charge		-	119	-	nC
Q <sub>ge</sub>	Gate to Emitter Charge	V <sub>CE</sub> = 400V, I <sub>C</sub> = 40A, V <sub>GE</sub> = 15V	-	13	-	nC
Q <sub>gc</sub>	Gate to Collector Charge	VGE - 10V	-	58	-	nC

# Electrical Characteristics of the Diode T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V <sub>FM</sub>	Diode Forward Voltage	I <sub>E</sub> = 20A	T <sub>C</sub> = 25°C	-	2.3	-	V
FIM			T <sub>C</sub> = 175°C	-	1.67	-	
E <sub>rec</sub>	Reverse Recovery Energy		T <sub>C</sub> = 175°C	-	48.9	-	uJ
t	t <sub>rr</sub> Diode Reverse Recovery Time	I <sub>F</sub> =20A, dI <sub>F</sub> /dt = 200A/μs	$T_C = 25^{\circ}C$	-	36	-	ns
ना			T <sub>C</sub> = 175°C	-	110	-	
Q <sub>rr</sub>	Q <sub>rr</sub> Diode Reverse Recovery Charge		T <sub>C</sub> = 25°C	-	46.8	-	nC
~ <sub>[]</sub>	2.000 November 1.000 November 9		T <sub>C</sub> = 175°C	-	445	-	0

**Figure 1. Typical Output Characteristics** 

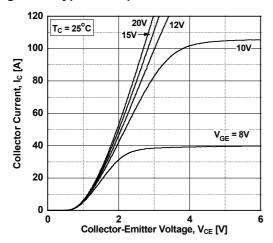


Figure 3. Typical Saturation Voltage Characteristics

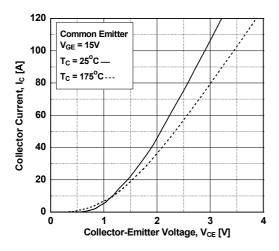
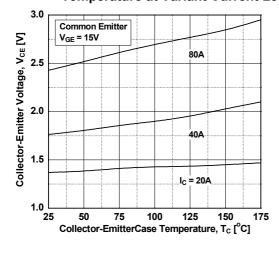
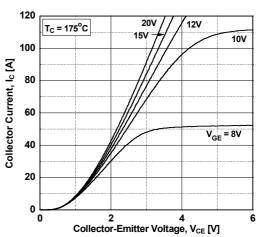


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level



**Figure 2. Typical Output Characteristics** 



**Figure 4. Transfer Characteristics** 

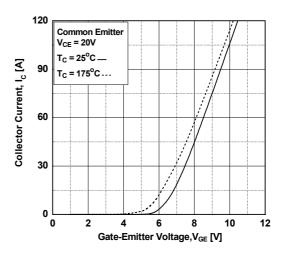


Figure 6. Saturation Voltage vs.  $V_{GE}$ 

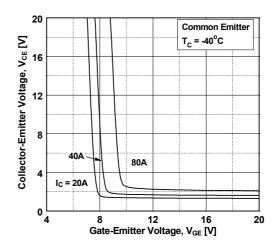
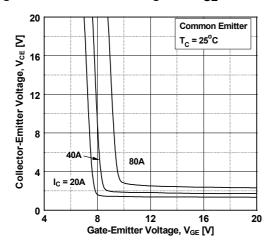


Figure 7. Saturation Voltage vs. V<sub>GE</sub>



**Figure 9. Capacitance Characteristics** 

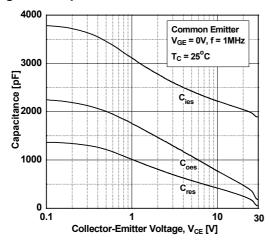


Figure 11. SOA Characteristics

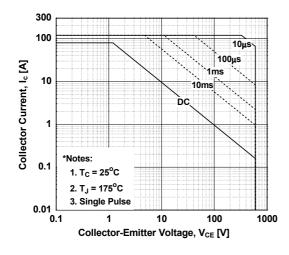


Figure 8. Saturation Voltage vs. V<sub>GE</sub>

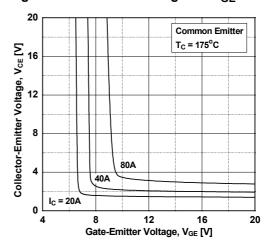


Figure 10. Gate charge Characteristics

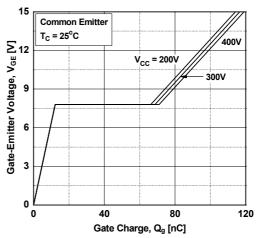


Figure 12. Turn-on Characteristics vs.
Gate Resistance

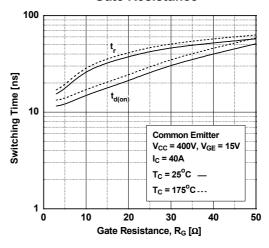


Figure 13. Turn-off Characteristics vs.
Gate Resistance

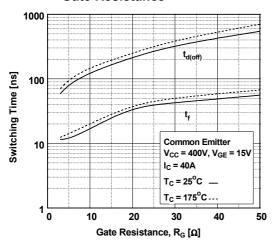


Figure 15. Turn-off Characteristics vs. Collector Current

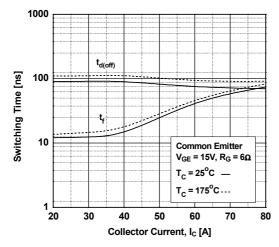


Figure 17. Switching Loss vs. Collector Current

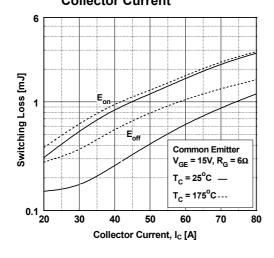


Figure 14. Turn-on Characteristics vs.
Collector Current

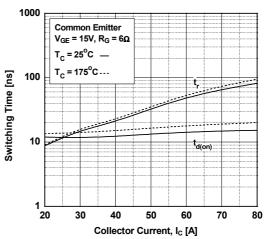


Figure 16. Switching Loss vs.

Gate Resistance

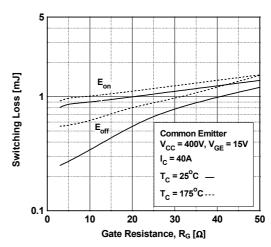


Figure 18. Turn off Switching SOA Characteristics

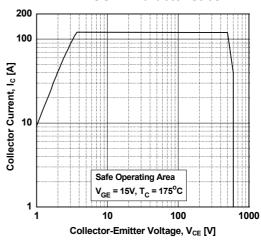


Figure 19. Current Derating

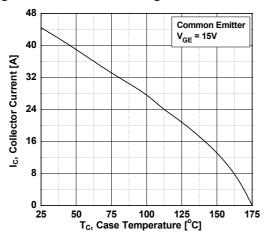


Figure 20. Power Dissipation

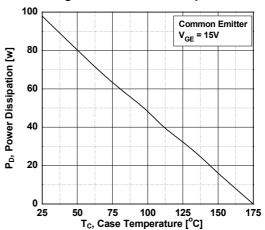


Figure 21. Load Current Vs. Frequency

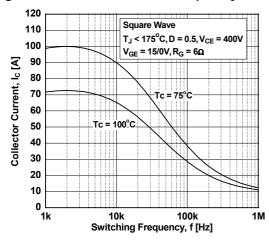


Figure 22. Forward Characteristics

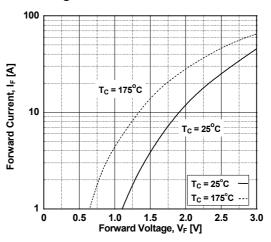


Figure 23. Reverse Current

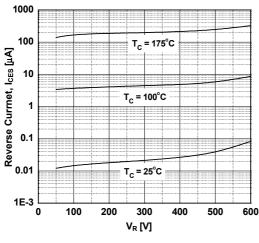


Figure 24. Stored Charge

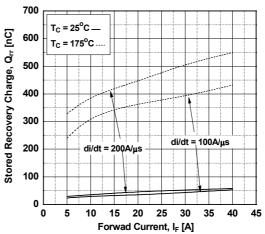


Figure 25. Reverse Recovery Time

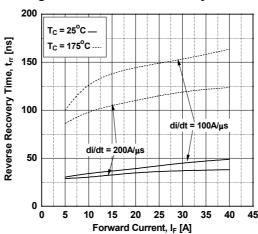


Figure 26.Transient Thermal Impedance of IGBT

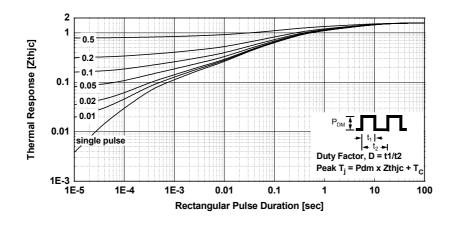
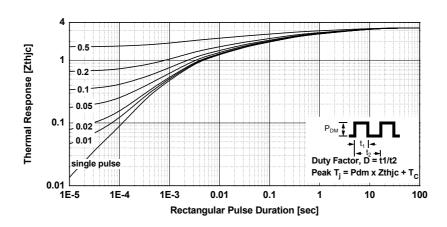
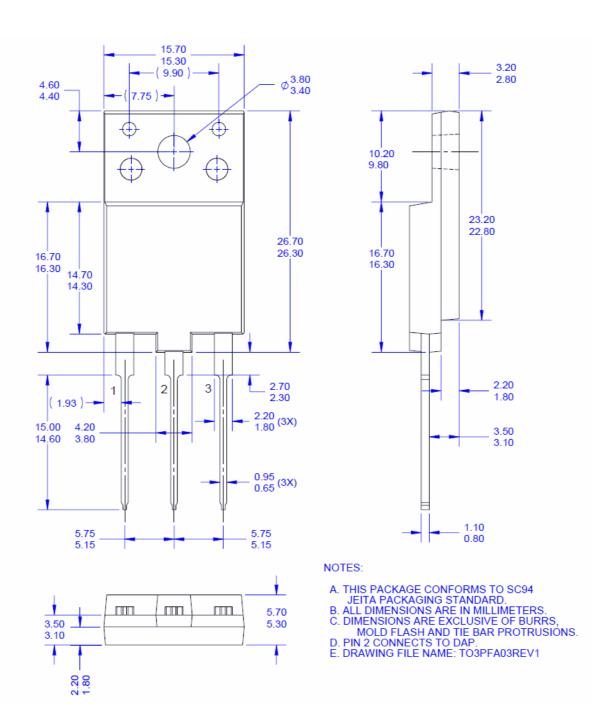


Figure 27. Transient Thermal Impedance of Diode



#### **Mechanical Dimensions**

# TO-3PF



Dimensions in Millimeters





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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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Rev. 164